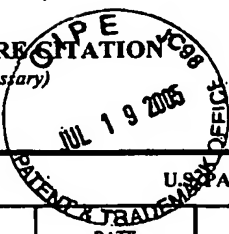


INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				Docket Number (Optional) F03-354-USDiv		Application Number 10/634,836	
				Applicant(s) Hisaki KATO, et al.			
				Filing Date August 6, 2003		Group Art Unit 2822	



U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

U.S. PATENT APPLICATION PUBLICATIONS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS								
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
KR		H7-7182	01/10/99	Japan			ABS	

OTHER DOCUMENTS		(Including Author, Title, Date, Pertinent Pages, Etc.)
KR		Japanese Office Action, dated May 24, 2005, with partial English translation
KR		NAKAMURA, et al., "Ridge-geometry InGaN multi-quantum-well-structure laser diodes", APPLIED PHYSICS LETTERS, September 2, 1996, Vol. 69, No. 10, pp. 1477-1479

EXAMINER <i>K. J. Rose</i>	DATE CONSIDERED <i>9 Feb 06</i>
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.